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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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NPN SILICON TRANSISTOR NE685M03

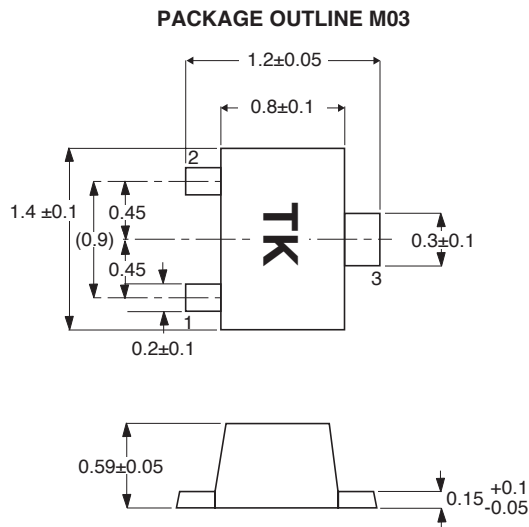
FEATURES

- **NEW M03 PACKAGE:**
 - Smallest transistor outline package available
 - Low profile/0.59 mm package height
 - Flat lead style for better RF performance
- **HIGH GAIN BANDWIDTH PRODUCT:**
 $f_T = 12 \text{ GHz}$
- **LOW NOISE FIGURE:**
 $NF = 1.5 \text{ dB at } 2 \text{ GHz}$

DESCRIPTION

The NEC's NE685M03 transistor is designed for low noise, high gain, and low cost requirements. This high f_T part is well suited for very low voltage/low current designs for portable wireless communications and cellular radio applications. NEC's new low profile/flat lead style "M03" package is ideal for today's portable wireless applications. The NE685 is also available in six different low cost plastic surface mount package styles.

OUTLINE DIMENSIONS (Units in mm)



PIN CONNECTIONS

1. Emitter
2. Base
3. Collector

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PART NUMBER EIAJ ¹ REGISTERED NUMBER PACKAGE OUTLINE		NE685M03 2SC5435 M03			
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
f_T	Gain Bandwidth at $V_{CE} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 2 \text{ GHz}$	GHz		12	
NF	Noise Figure at $V_{CE} = 3 \text{ V}$, $I_C = 3 \text{ mA}$, $f = 2 \text{ GHz}$	dB		1.5	2.5
IS_{21E}^2	Insertion Power Gain at $V_{CE} = 3 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 2 \text{ GHz}$	dB	7	9	
h_{FE}^2	Forward Current Gain at $V_{CE} = 3 \text{ V}$, $I_C = 10 \text{ mA}$		75		140
I_{CBO}	Collector Cutoff Current at $V_{CB} = 5 \text{ V}$, $I_E = 0$	μA			0.1
I_{EBO}	Emitter Cutoff Current at $V_{EB} = 1 \text{ V}$, $I_C = 0$	μA			0.1
CRE^3	Feedback Capacitance at $V_{CB} = 3 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$	pF		0.4	0.7

Notes:

1. Electronic Industrial Association of Japan.
2. Pulsed measurement, pulse width $\leq 350 \mu\text{s}$, duty cycle $\leq 2\%$.
3. Capacitance is measured with emitter and case connected to the guard terminal at the bridge.

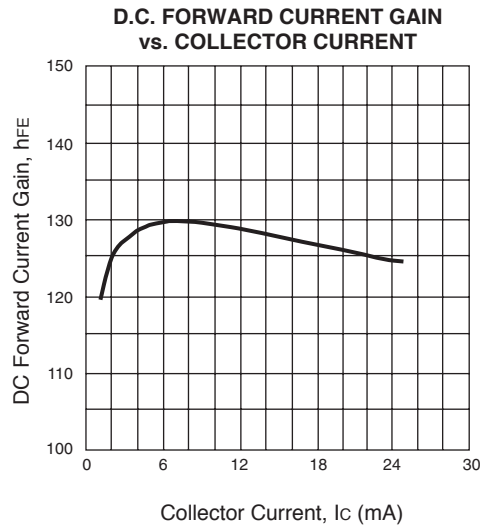
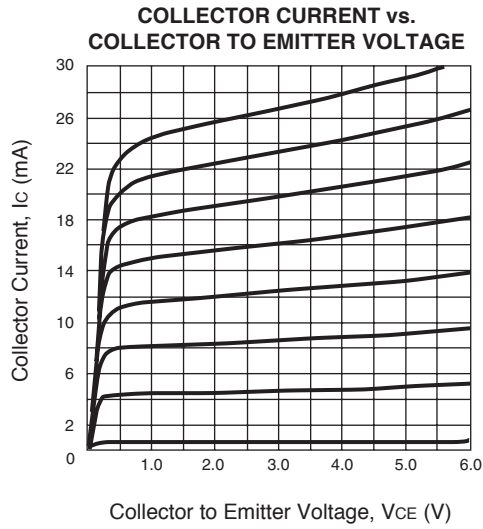
ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CB0}	Collector to Base Voltage	V	9
V _{CE0}	Collector to Emitter Voltage	V	5
V _{EB0}	Emitter to Base Voltage	V	2
I _C	Collector Current	mA	30
P _T	Total Power Dissipation	mW	125
T _J	Junction Temperature	°C	150
T _{STG}	Storage Temperature	°C	-65 to +150

Note:

1. Operation in excess of any one of these parameters may result in permanent damage.

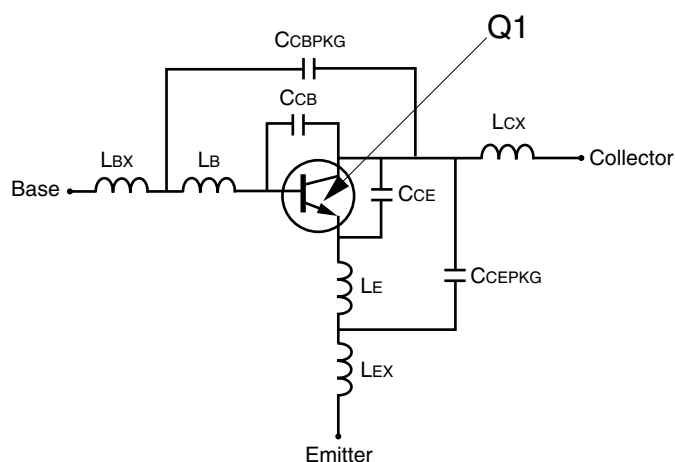
TYPICAL PERFORMANCE CURVES (T_A = 25°C)



ORDERING INFORMATION

PART NUMBER	QUANTITY
NE685M03-A	
NE685M03-T1-A	

SCHEMATIC



BJT NONLINEAR MODEL PARAMETERS (1)

Parameters	Q1	Parameters	Q1
IS	8.98e-17	MJC	0.19
BF	107.1	XCJC	0
NF	0.99	CJS	0
VAF	22	VJS	0.75
IKF	0.55	MJS	0
ISE	1e-6	FC	0.5
NE	31.10	TF	4e-12
BR	16.06	XTF	12
NR	0.98	VTF	1
VAR	6	ITF	0.04
IKR	8.02e-3	PTF	120
ISC	0	TR	1e-9
NC	2	EG	1.11
RE	0.6	XTB	0
RB	10	XTI	3
RBM	8.34	KF	0
IRB	0.009	AF	1
RC	5.07		
CJE	0.50e-12		
VJE	0.95		
MJE	0.5		
CJC	0.11e-12		
VJC	0.56		

(1) Gummel-Poon Model

UNITS

Parameter	Units
time	seconds
capacitance	farads
inductance	henries
resistance	ohms
voltage	volts
current	amps

ADDITIONAL PARAMETERS

Parameters	68533
CcB	0.13e-12
CcE	0.14e-12
Lb	0.3e-9
LE	0.8e-9
CcBPKG	0.08e-12
CcEPKG	0.08e-12
LbX	0.12e-9
LcX	0.10e-9
LEx	0.12e-9

MODEL RANGE

Frequency: 0.1 to 4.0 GHz
 Bias: $V_{CE} = 0.5 \text{ V to } 3 \text{ V}$, $I_C = 0.5 \text{ mA to } 20 \text{ mA}$
 Date: 11/98

Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

EXCLUSIVE NORTH AMERICAN AGENT FOR NEC RF, MICROWAVE & OPTOELECTRONIC SEMICONDUCTORS

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06/10/2002

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL’s understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
		-A	-AZ
Lead (Pb)	< 1000 PPM	Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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In no event shall CEL’s liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.

See CEL Terms and Conditions for additional clarification of warranties and liability.